

500V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

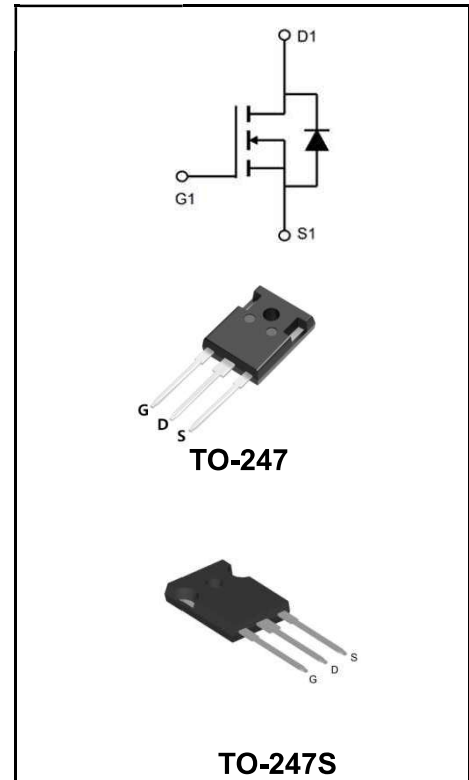
I_D	28A
V_{DSS}	500V
R_{DS(on)-typ(@V_{GS}=10V)}	<0.18Ω (Type:0.14Ω)

Features

- ◆Fast Switching
- ◆Low ON Resistance
- ◆Low Gate Charge
- ◆100% Single Pulse avalanche energy Test
- ◆LeadfreeincomplywithEURoHS2011/65/EUdirectives

Mechanical Data

- ◆Case: Molded plastic
- ◆Mounting Position: Any
- ◆Molded Plastic: UL Flammability Classification Rating 94V-0
- ◆Solder bath temperature275℃maximum,10s per JESD22-106



Product Specification Classification

Part Number	Package	Marking	Pack
YFW28N50AP	TO-247	YFW 28N50AP XXXXX	30PCS/Tube
YFW28N50APS	TO-247S	YFW 28N50APS XXXXX	30PCS/Tube

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
		247/247S	
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	±30	V
Continue Drain Current	I_D	28	A
-Continuous (TC = 100°C)		19	
Pulsed Drain Current (Note1)	I_{DM}	100	A
Power Dissipation	P_D	300	W
-Derate above 25°C		2.5	
Single Pulse Avalanche Energy (Note2)	E_{AS}	1500	mJ
Avalanche Current (Note 1)	I_{AR}	28	A
Repetitive Avalanche Energy (Note 1)	E_{AS}	32	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	R_{θJC}	0.42	°C/W
Thermal Resistance, Junction to Ambient	R_{θJA}	40	°C/W

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	BV_{DSS}	500	-	-	V
Breakdown Voltage Temperature Coefficient	I _D =250μA (Referenced to 25°C)	$\frac{\Delta BV_{DSS}}{\Delta T_J}$	-	0.5	-	V/°C
Drain-Source Leakage Current	V _{DS} = 500 V, V _{GS} = 0 V	I_{DSS}	-	-	1	uA
	V _{DS} = 400 V, T _C = 125°C		-	-	10	
Gate Leakage Current	V _{GS} = ± 30 V, V _{DS} = 0 V	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	V_{GS(th)}	2	0	4	V
Drain-Source On-State Resistance	V _{GS} = 10 V, I _D = 14A	R_{DS(on)}	-	0.14	0.18	Ω
Forward Transconductance	V _{DS} = 15 V, I _D = 14 A	g_{fs}	-	18	-	S
Input Capacitance	V _{GS} = 0 V, V _{DS} = 25 V, f = 1MHz	C_{iss}	-	4611	-	pF
Output Capacitance		C_{OSS}	-	225	-	
Reverse Transfer Capacitance		C_{rss}	-	12	-	
Turn-on Delay Time	I _D = 28, V _{DD} = 250V, R _G =25Ω(Note3,4)	td(ON)	-	37.2	-	nS
Rise Time		tr	-	64.4	-	
Turn-Off Delay Time		td(OFF)	-	86.8	-	
Fall Time		tf	-	46	-	
Total Gate Charge	I _D =28 A, V _{DD} = 400 V, V _{GS} = 10 V(Note3,4)	Q_G	-	121	-	nC
Gate to Source Charge		Q_{GS}	-	20	-	
Gate to Drain Charge		Q_{GD}	-	32	-	

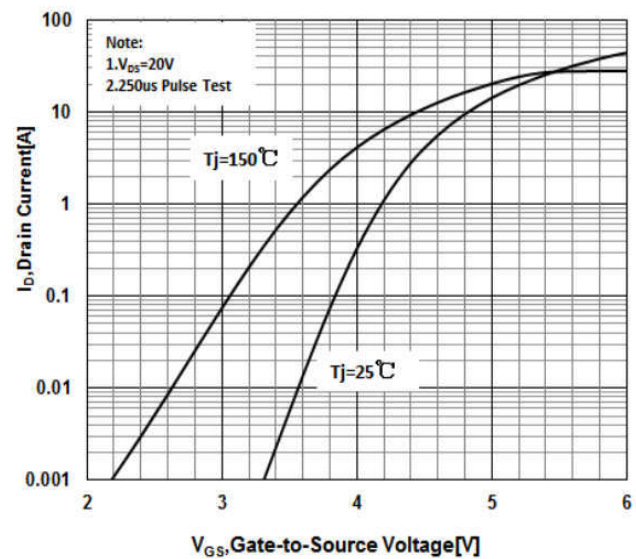
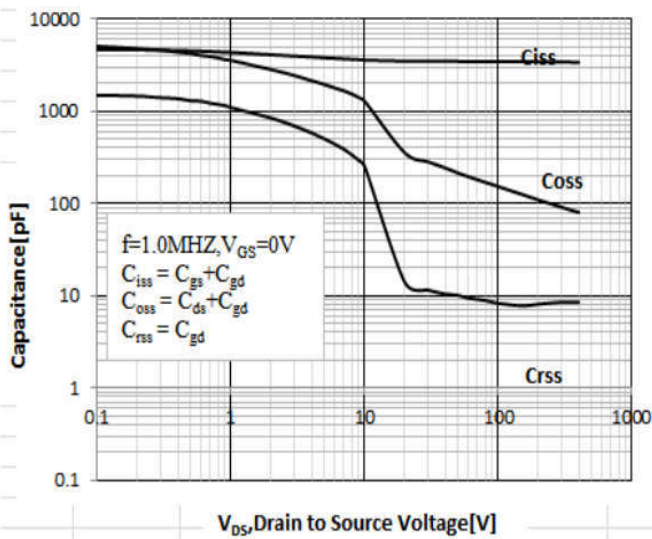
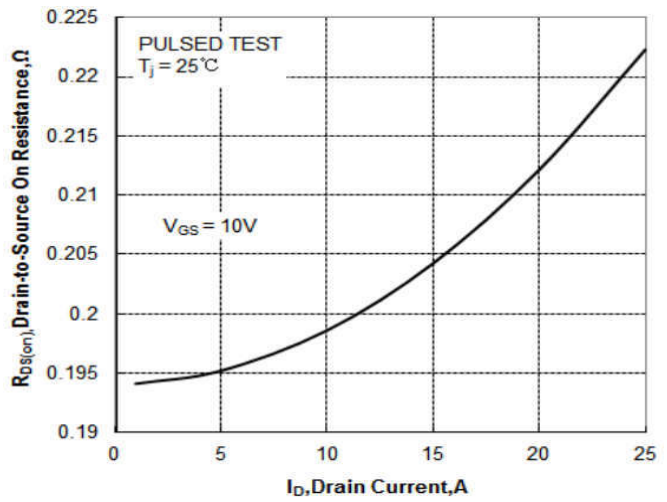
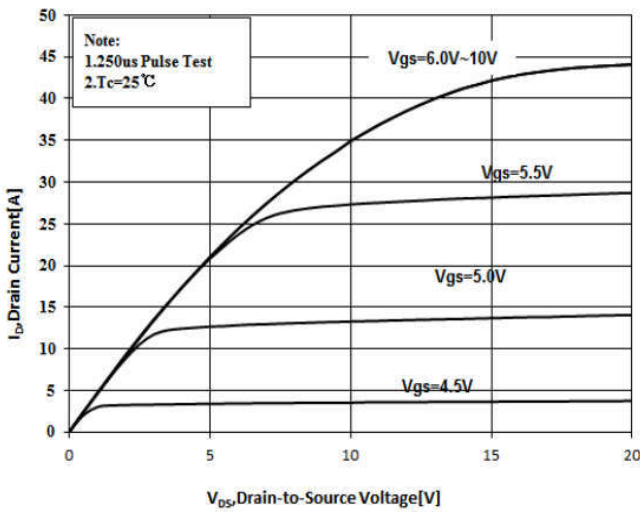
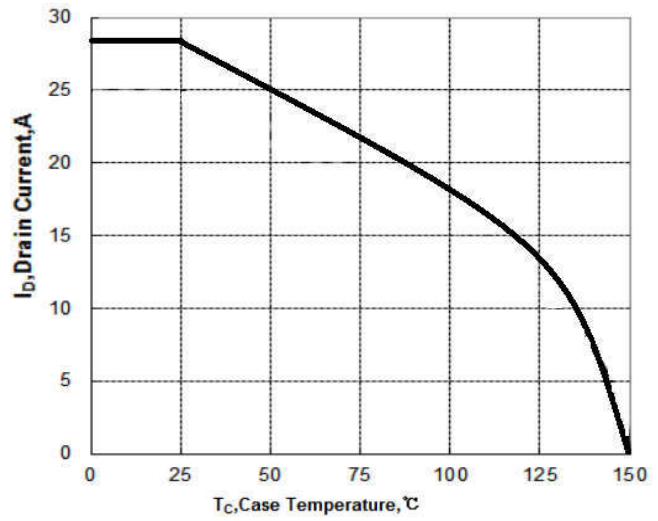
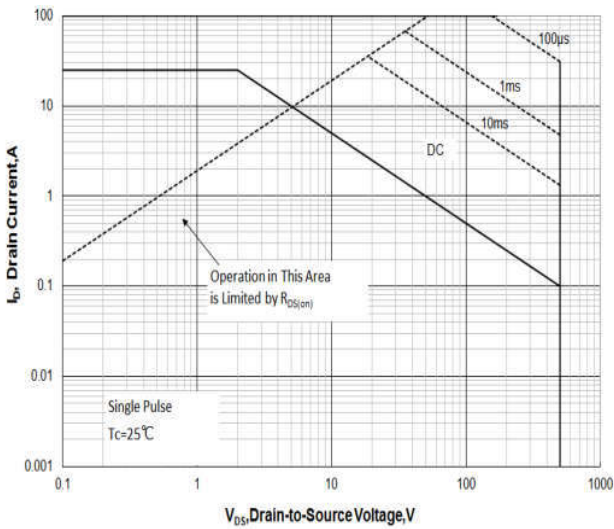
Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Maximun Body-Diode Continuous Current		I_S	-	-	25	A
Maximun Body-Diode Pulsed Current		I_{SM}	-	-	100	A
Drain-Source Diode Forward Voltage	I_{SD} = 28A	V_{SD}	-	-	1.5	V
Reverse Recovery Time	I_{SD} = 28A, V_{GS} = 0 V, dI_F / dt = 100 A/μs	trr	-	490	-	nS
Reverse Recovery Charge		Qrr	-	6.2	-	uC

Note:

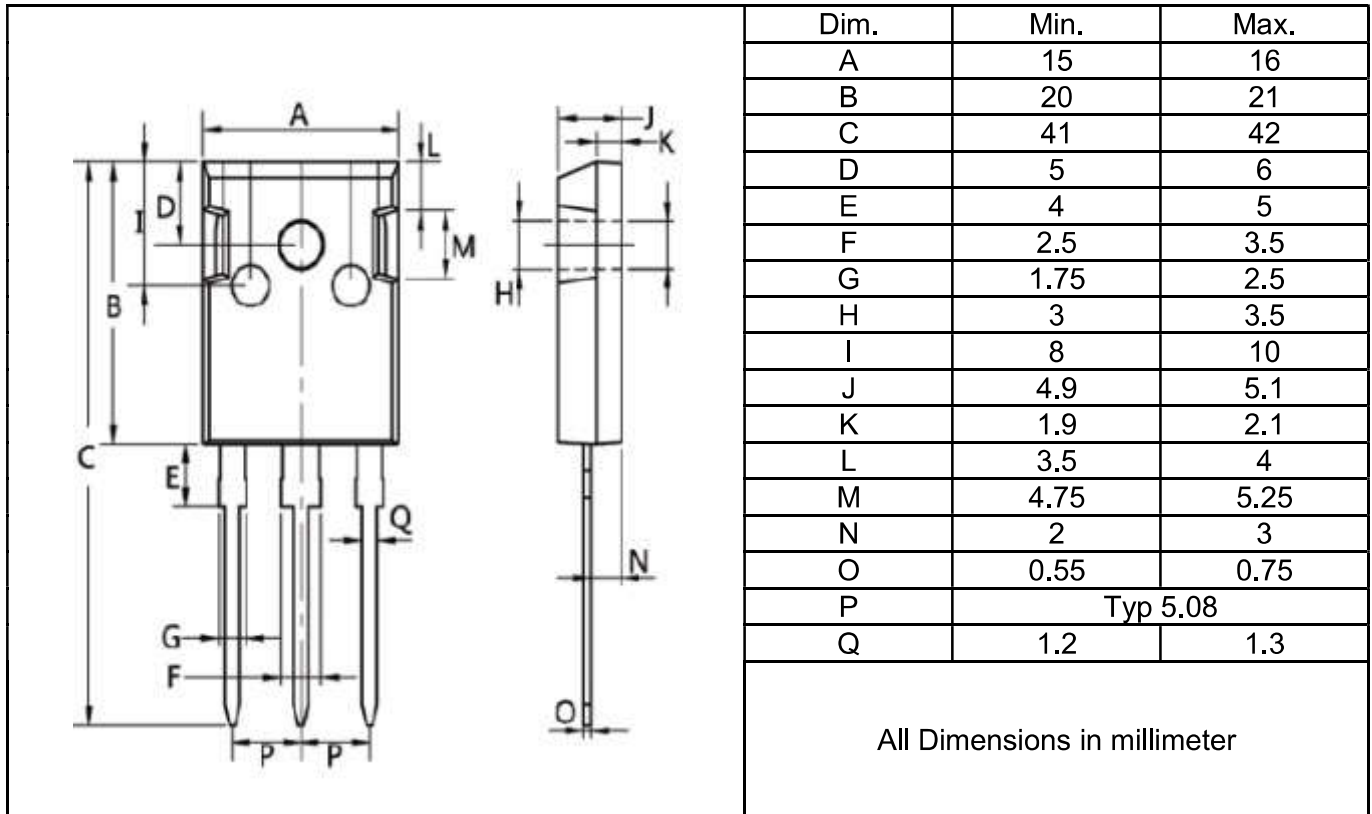
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. IAS = 28 A, VDD = 50 V, L = 4mH, RG = 25Ω, starting TJ = 25°C.
3. ulse test: Pulse Width ≤300 μ s, Duty Cycle≤2%.
4. Essentially Independent of Operating Temperature.

Ratings and Characteristic Curves



Package Outline Dimensions Millimeters

TO-247



TO-247S

